

Oct. 23, 2020
15:00 - 15:15

Analog Circuit Session 1

Operation and Stability Analysis of Temperature-Insensitive MOS Reference Current Source with Self-Bias Circuit

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Jedat Inc.

Outline

- **Research Background**
- **MOS Drain Current**
Temperature Characteristics
- **Temperature-Insensitive Current Source**
- **Proposed Circuit using Self-Bias**
- **Stability Verification**
- **Conclusion**

Outline

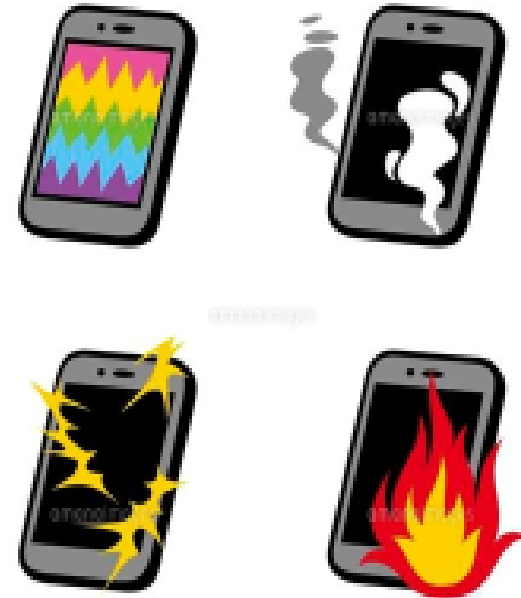
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Research Background

Reliability issues in electronic circuits

- Process
- Voltage
- **Temperature**

We focus on



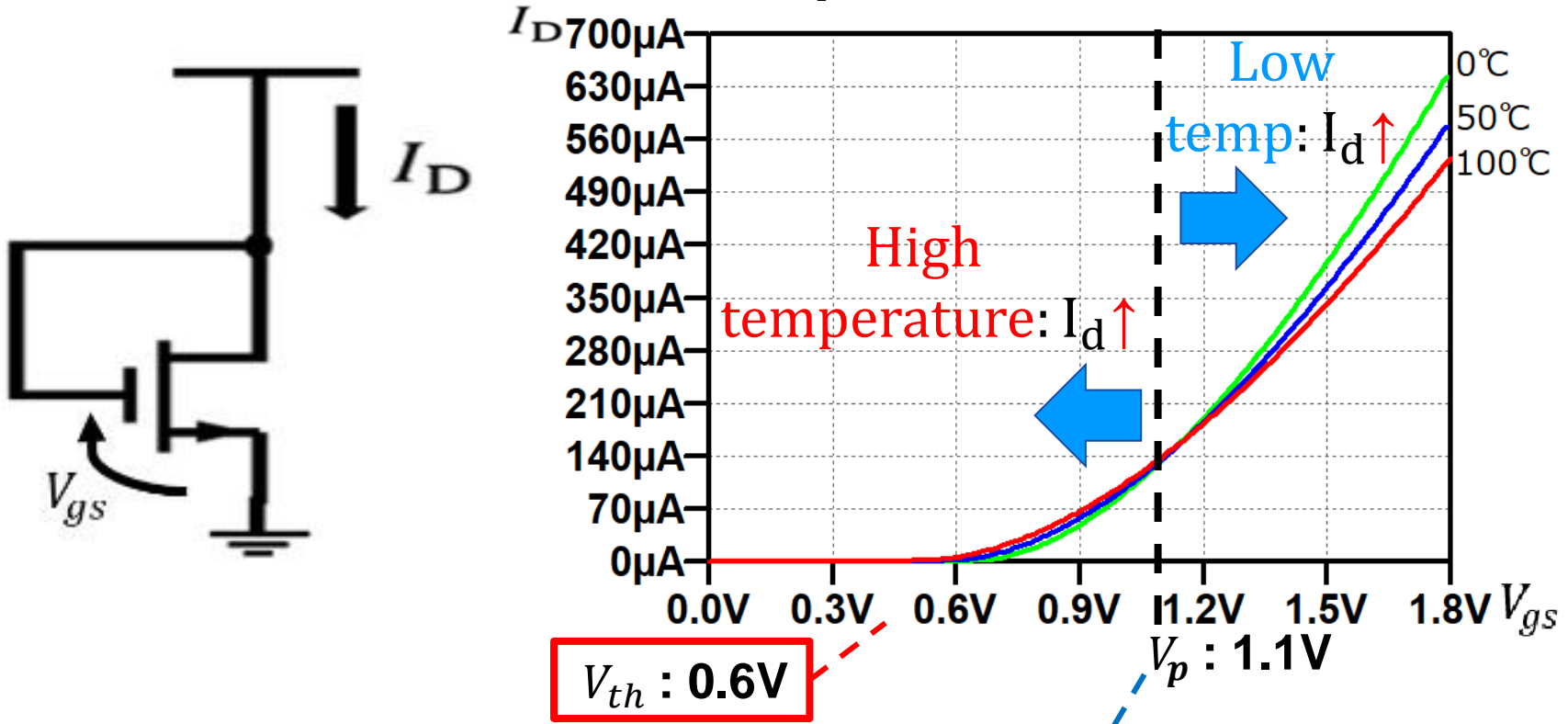
**Temperature-insensitive
current source**

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MOS Drain Current and Gate Voltage

Simulated drain current temperature characteristics

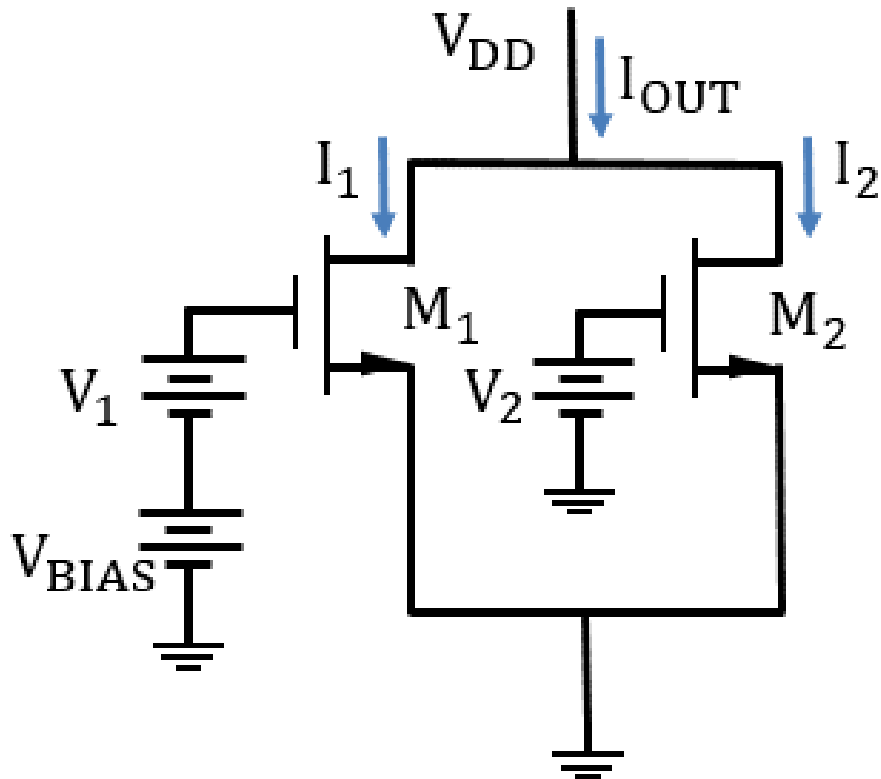


Gate voltage: Drain current is fixed against temperature change

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Concept of Temperature-Insensitive Current Source

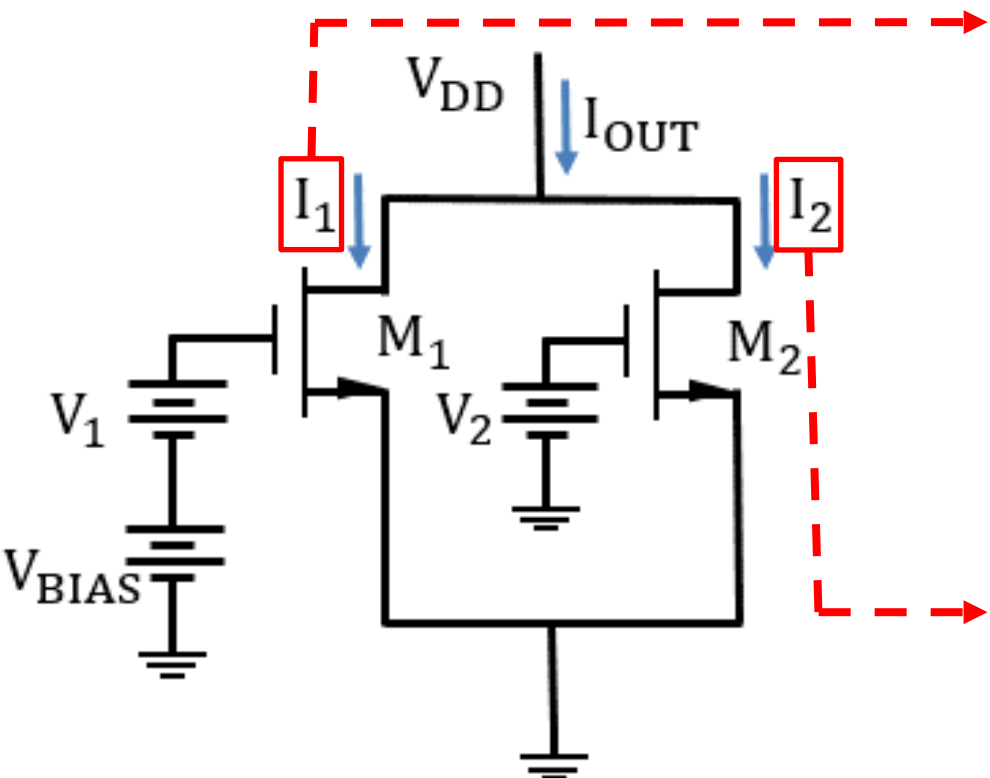


Simulation conditions

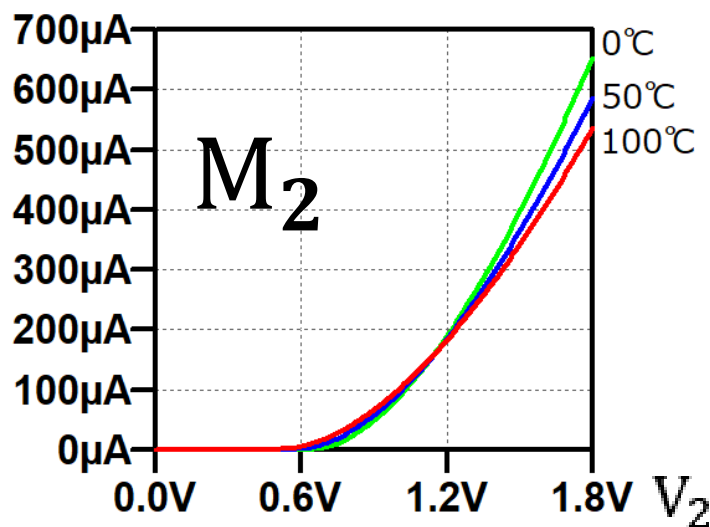
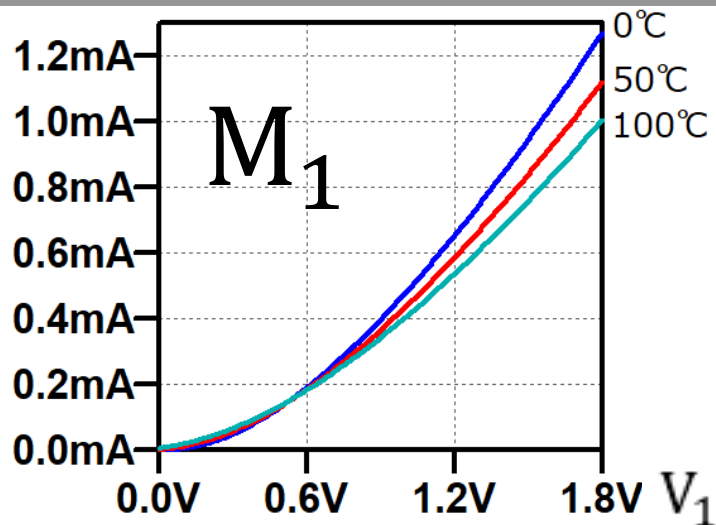
V_{BIAS}	0.6 V
V_1, V_2	0 ~ 1.8 V
V_{DD}	5.0 V
M_1, M_2	W=20 μm , L=2.0 μm

Proposed circuit concept

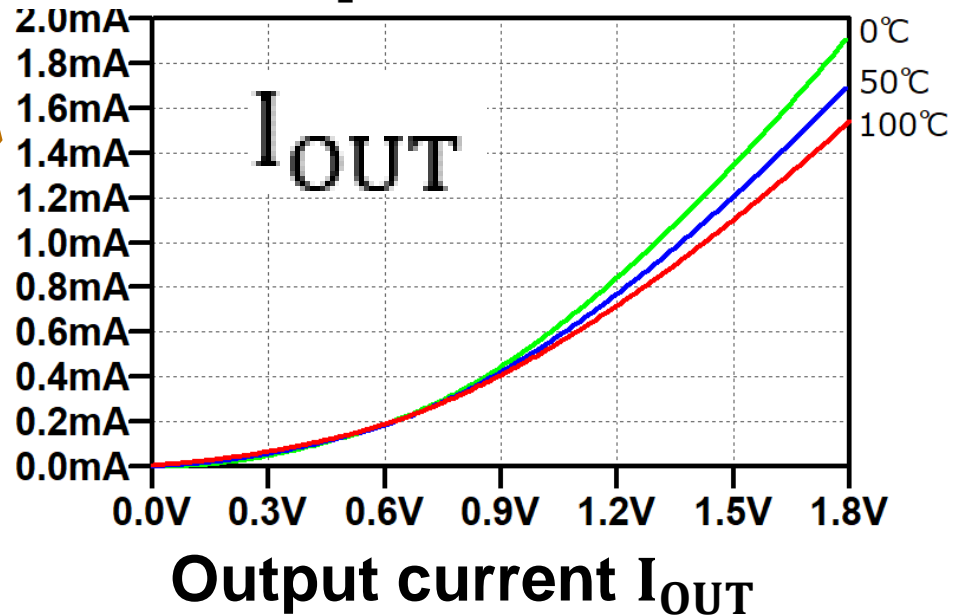
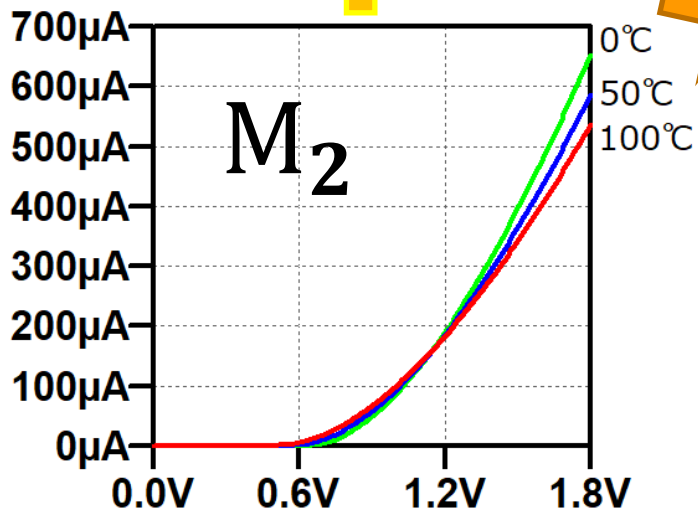
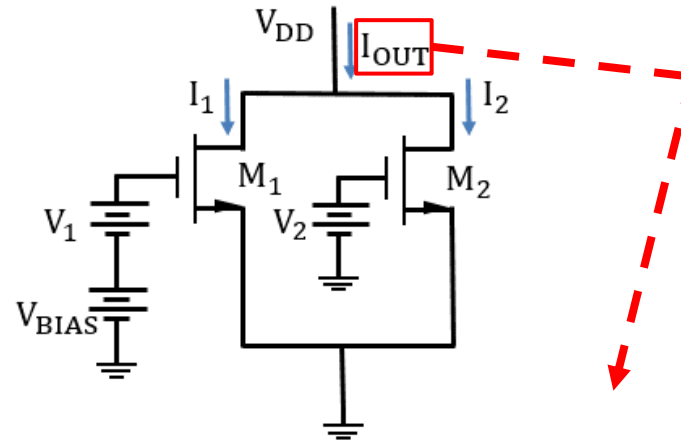
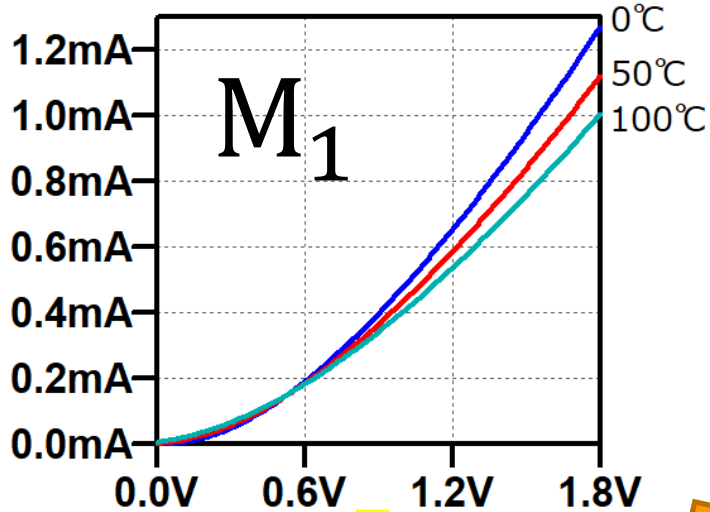
$I_D - V_{GS}$ Characteristics of Two MOSFETs



Temperature characteristics are shifted.



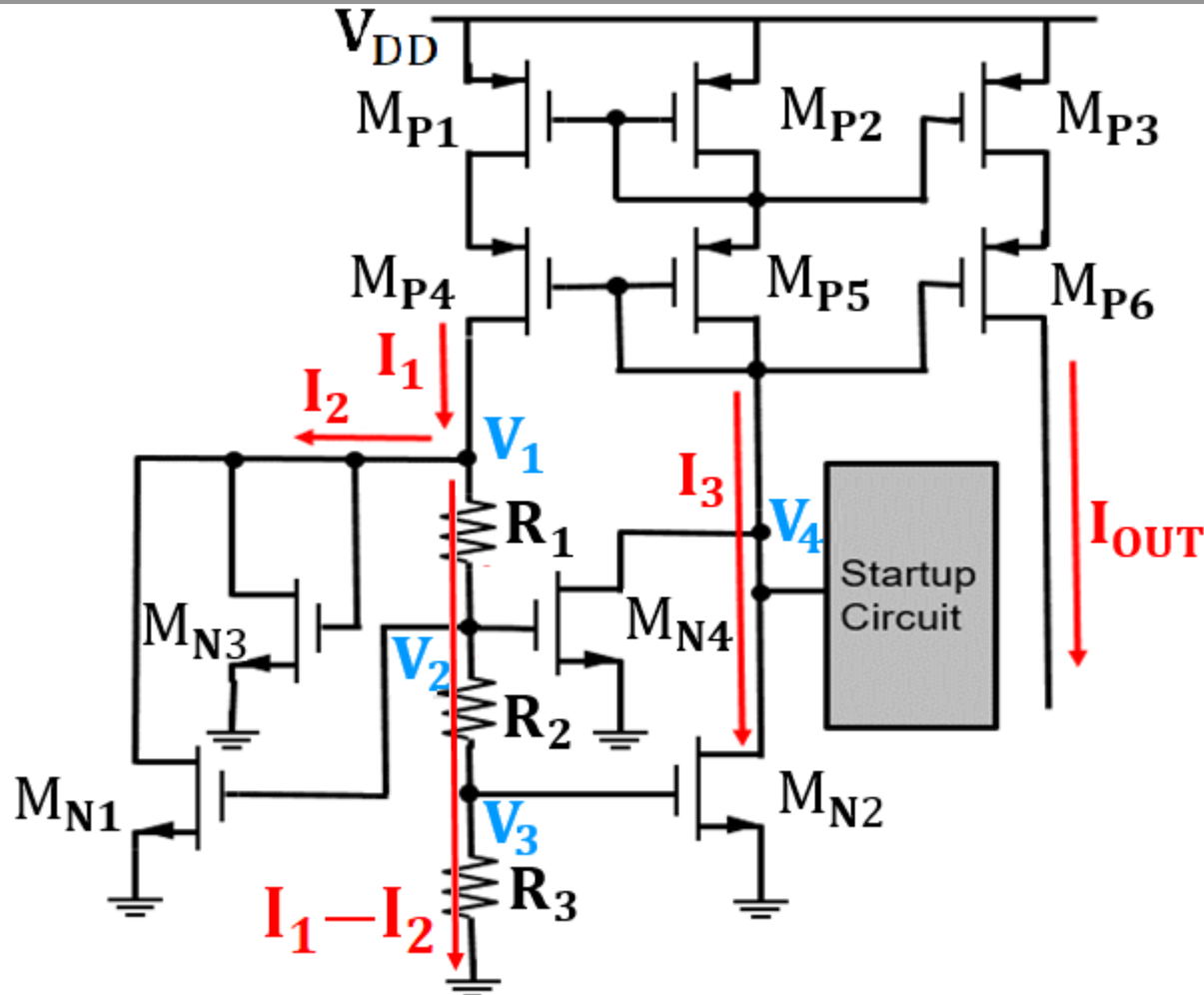
Cancellation of Temperature Characteristics



Outline

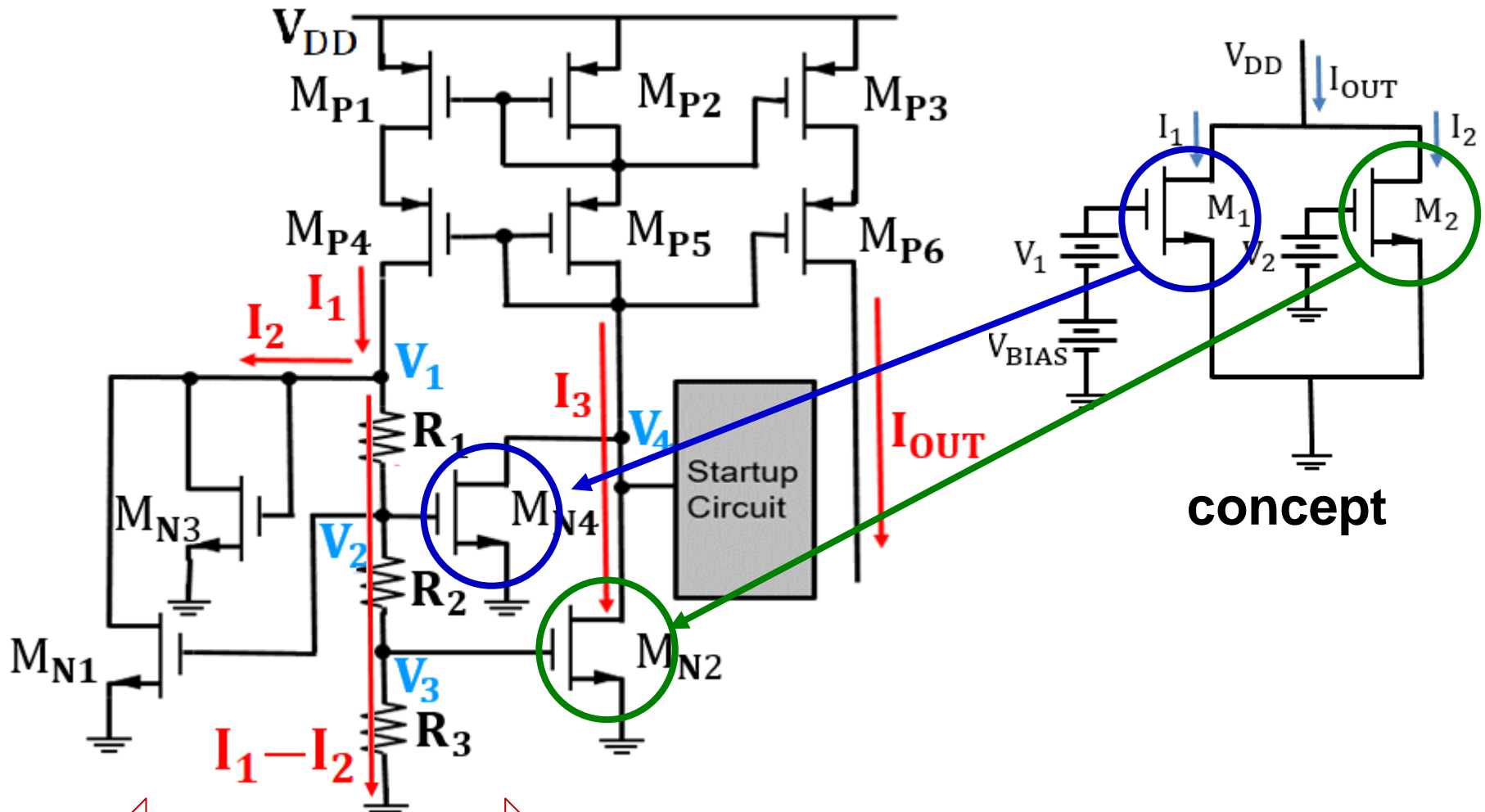
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Proposed circuit



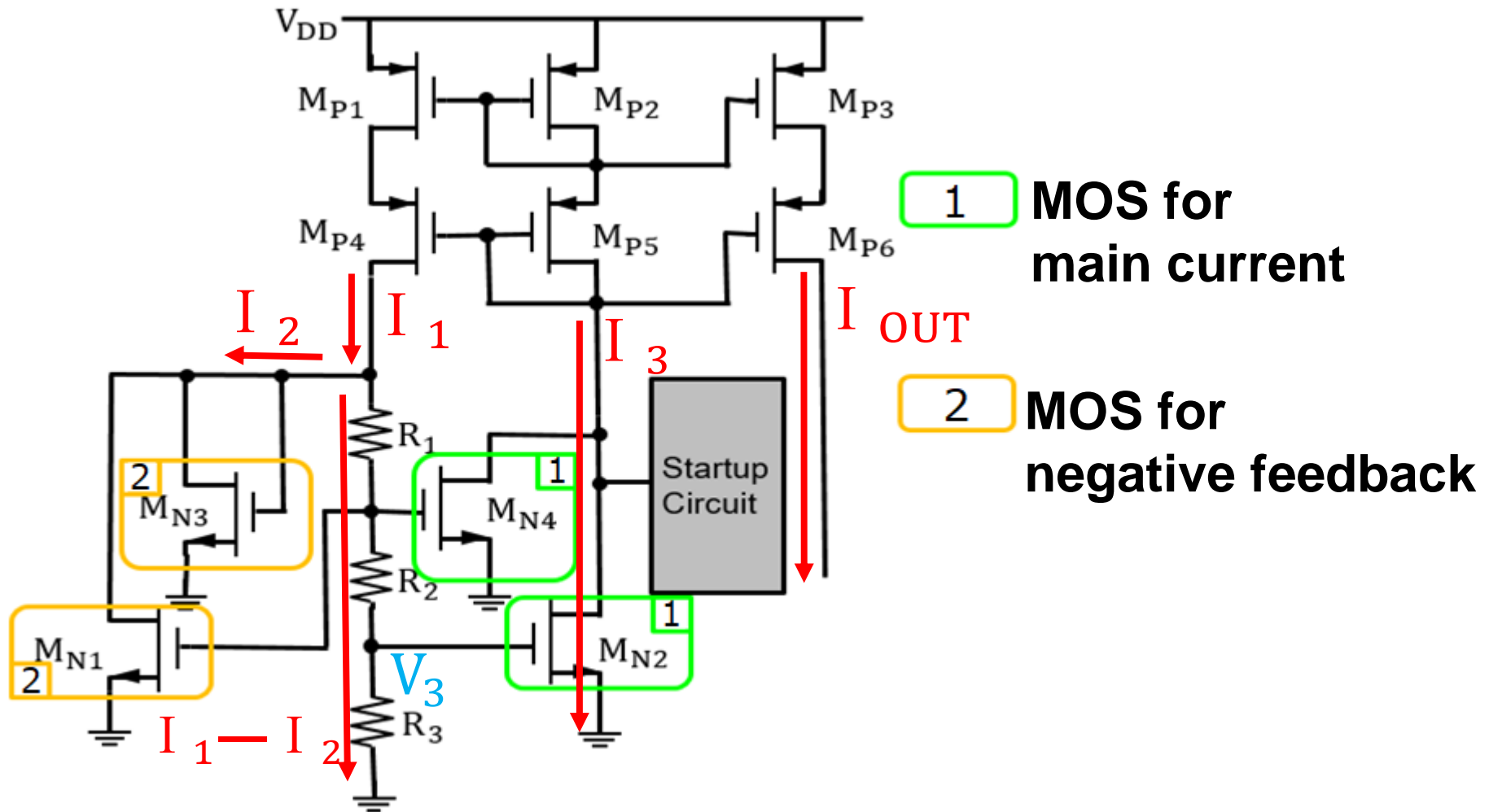
Proposed circuit using self-bias

Compared to the concept circuit

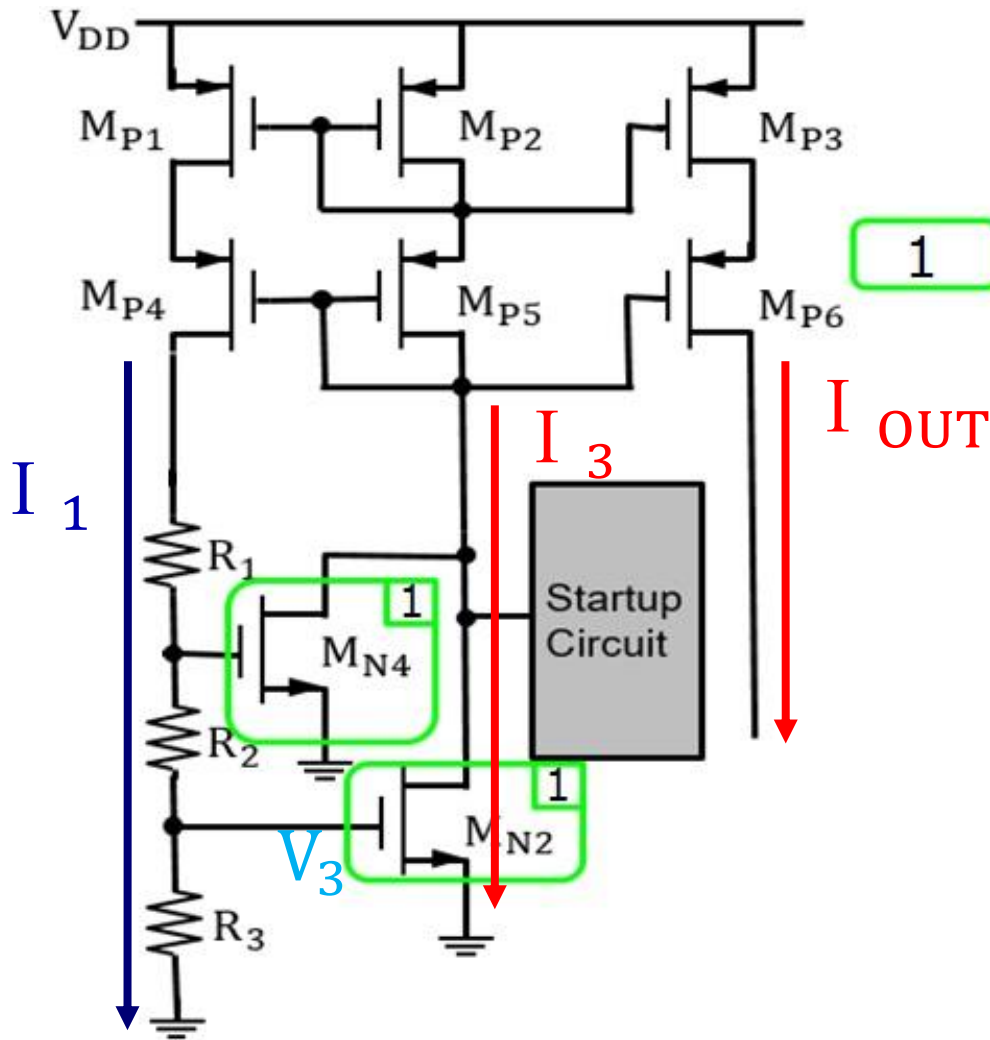



Self-bias circuit

Negative Feedback for Self-Bias



Self-Bias Problem



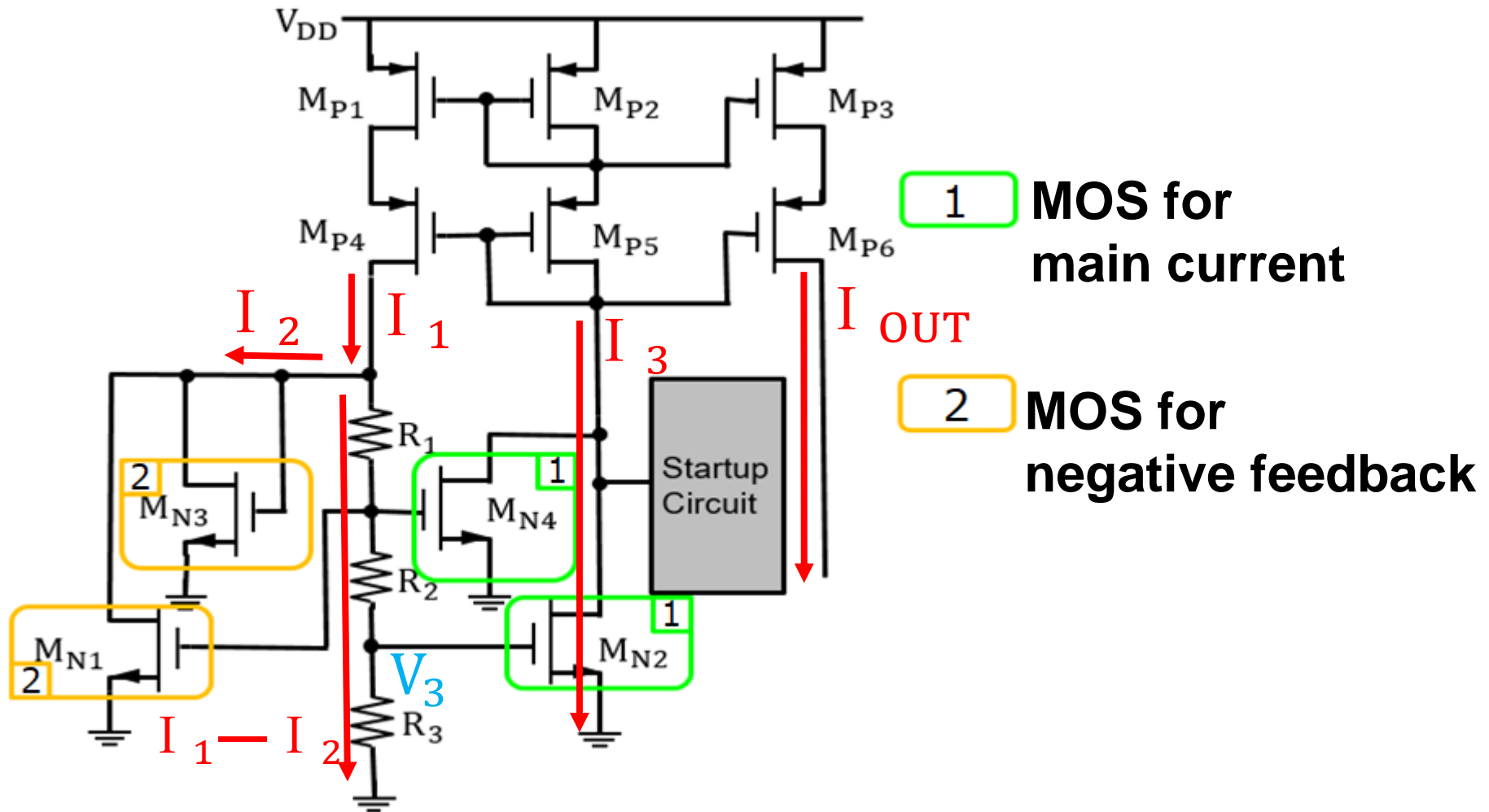
1 MOS for
 main current

- **I₃** increase
- **I₁** increase
- **I₃** increase

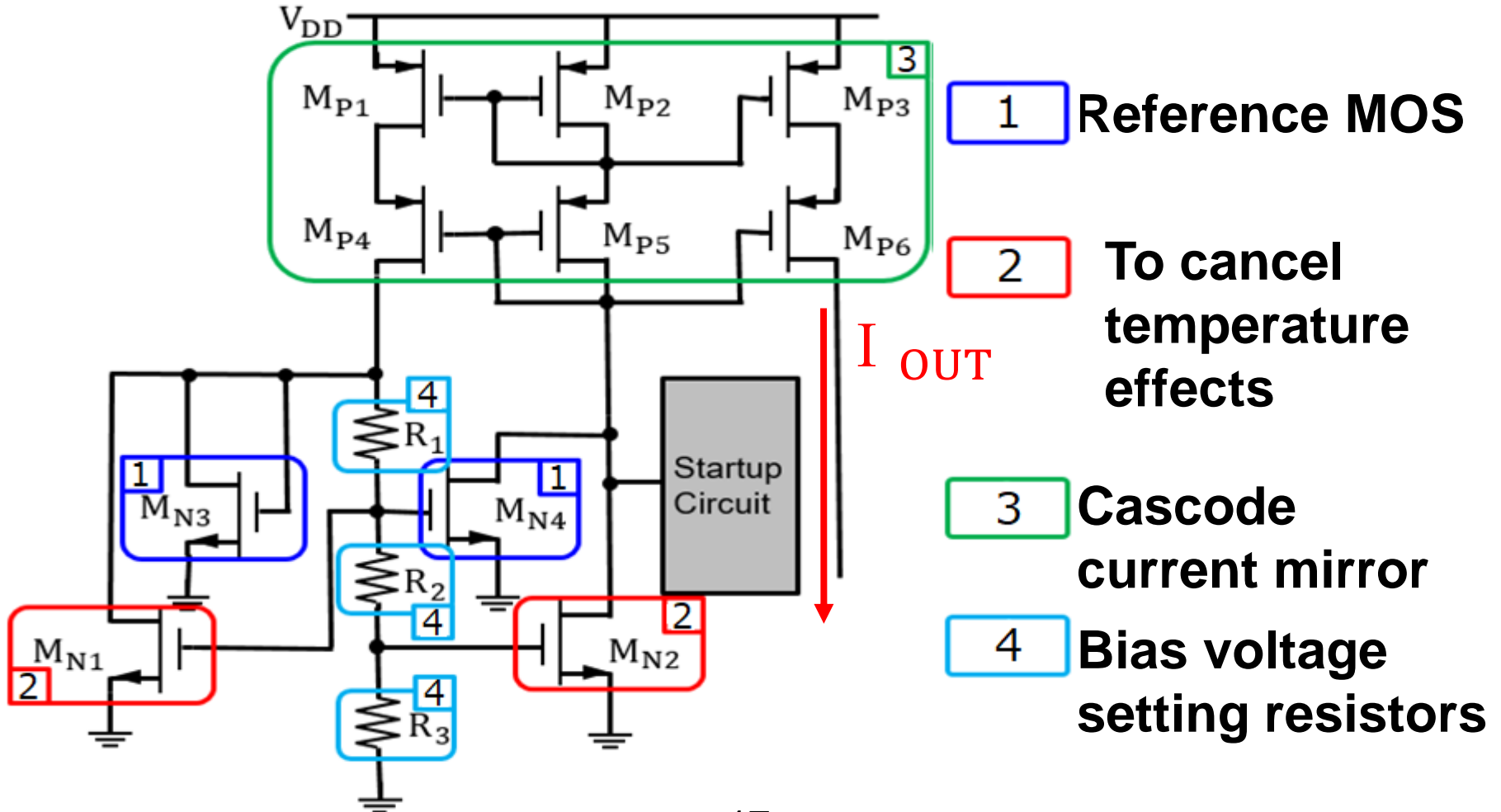


Positive Feedback !

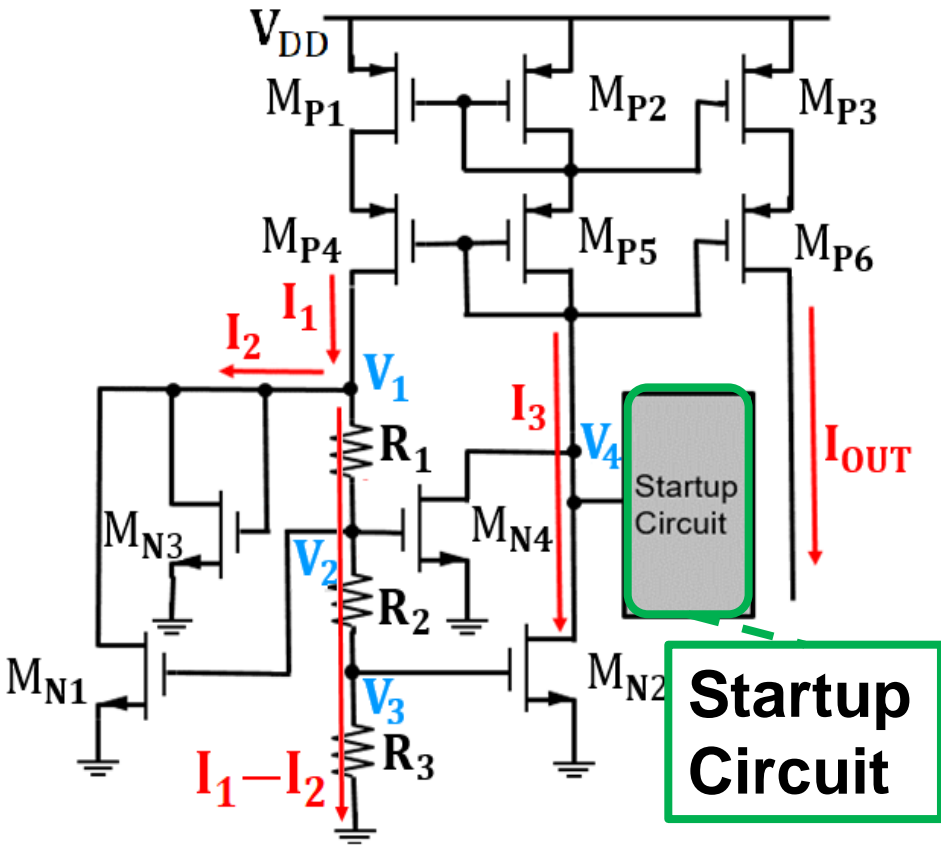
Negative Feedback for Self-Bias



Roles of MOS FETs and Resistors

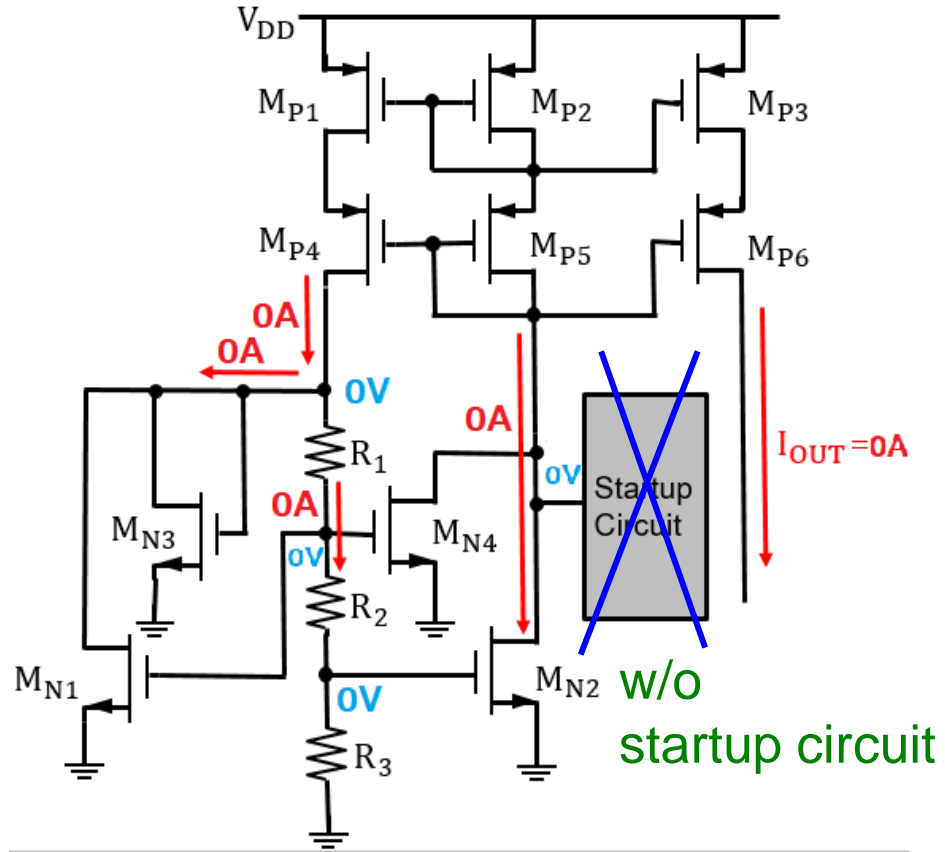


Startup Circuit is Needed



I_{OUT} conduction state

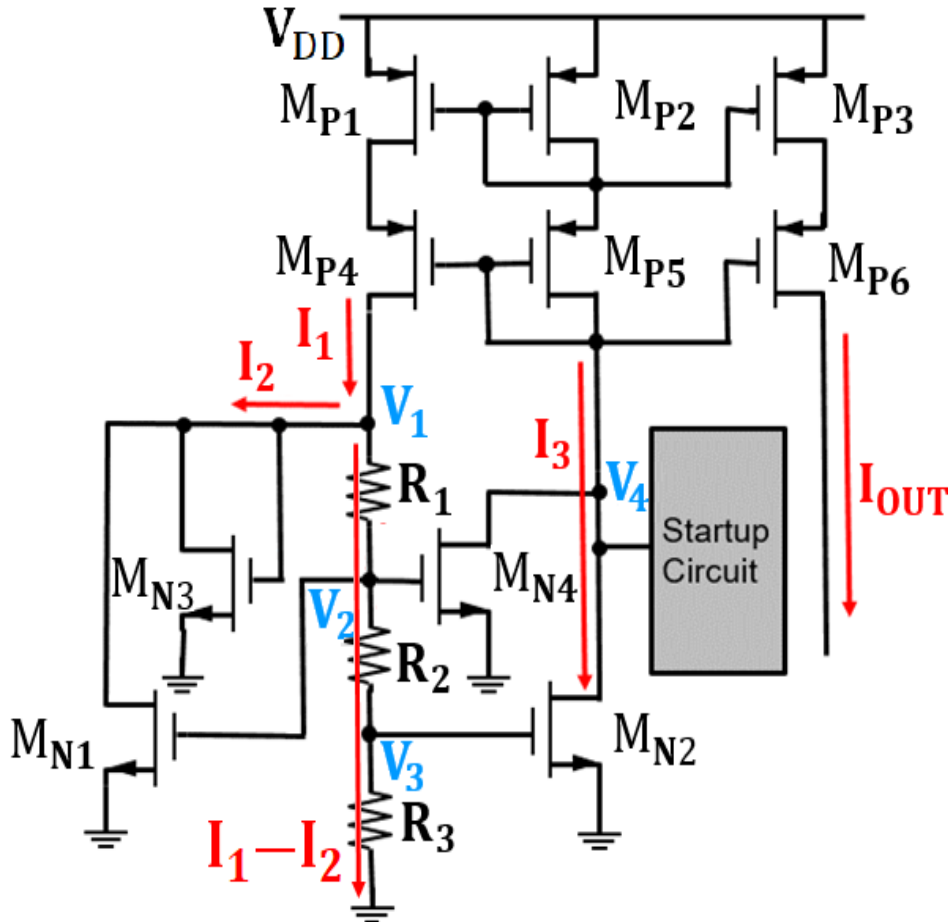
Proper operation



$I_{OUT} = 0$

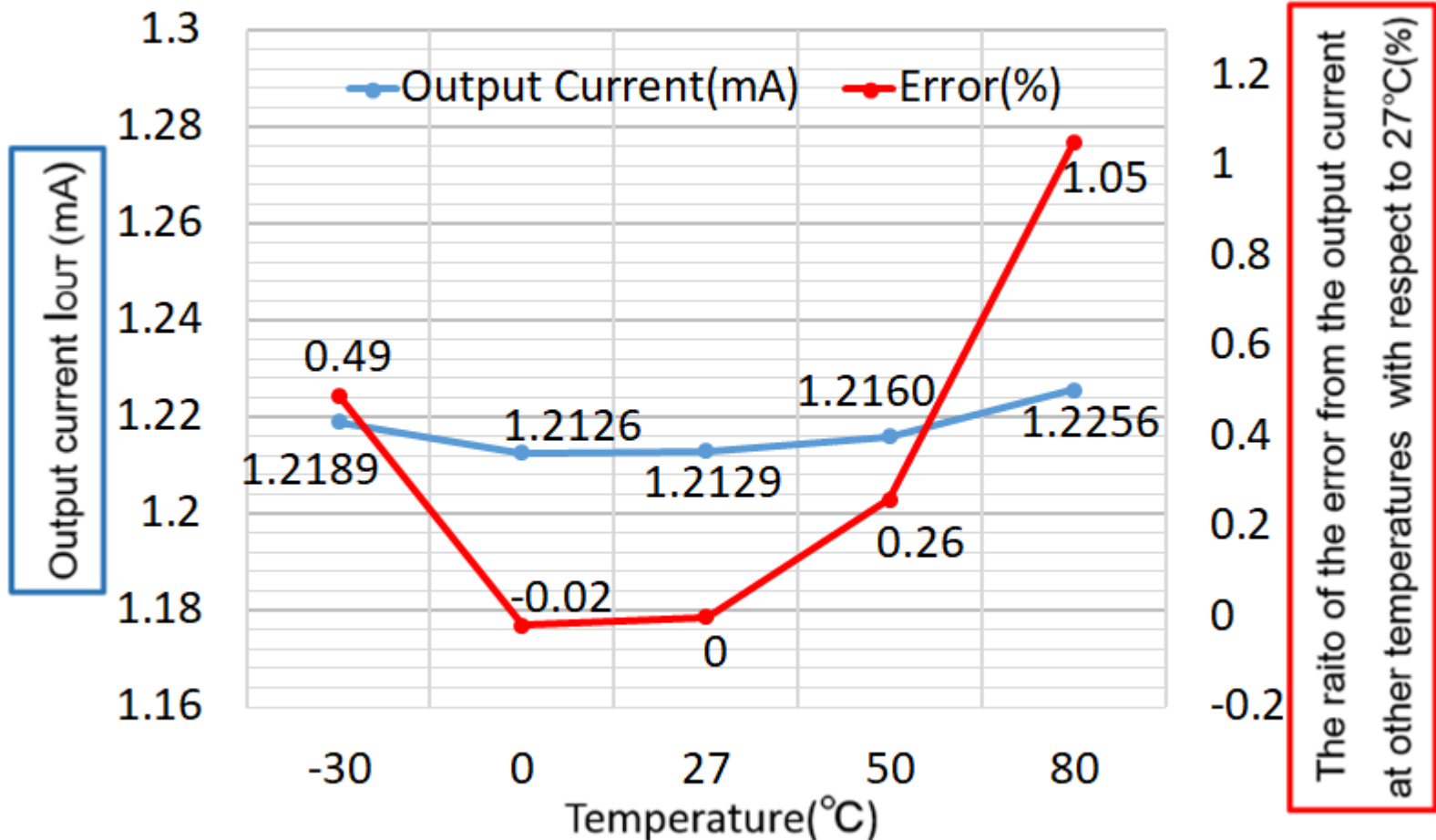
Malfunction

SPICE Simulation Conditions



$M_{P1} \sim M_{P6}$	$W=800\mu\text{m}, L=2.0\mu\text{m}$
M_{N1}, M_{N3}	$W=0.25\mu\text{m}, L=2.0\mu\text{m}$
M_{N2}	$W=200\mu\text{m}, L=2.0\mu\text{m}$
M_{N4}	$W=20\mu\text{m}, L=2.0\mu\text{m}$
R_1	5.0 k Ω
R_2	1.61 k Ω
R_3	1.5 k Ω
V_{DD}	5.0 V

Output Current I_{OUT} Deviation

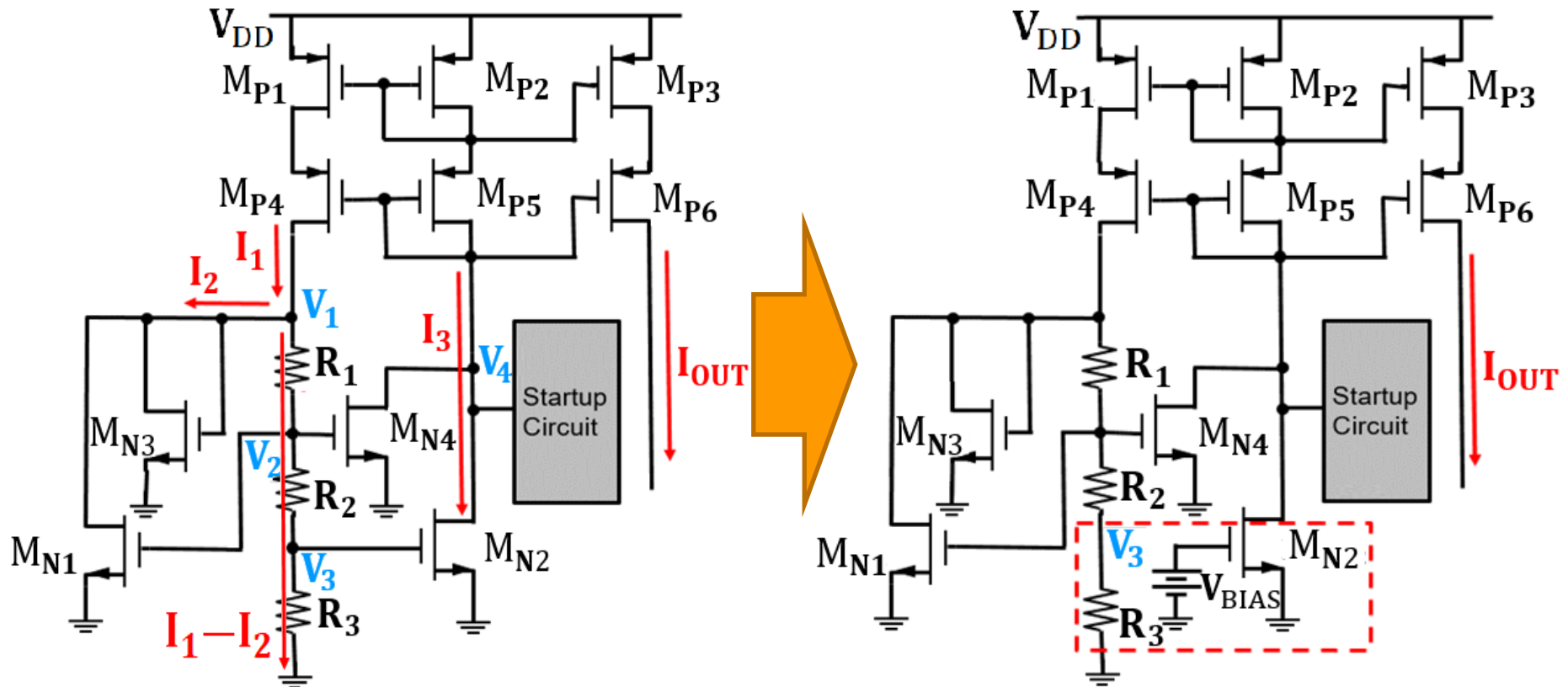


Output current I_{OUT} against temperature change from current @ 27 °C.

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Feedback Loop Disconnection

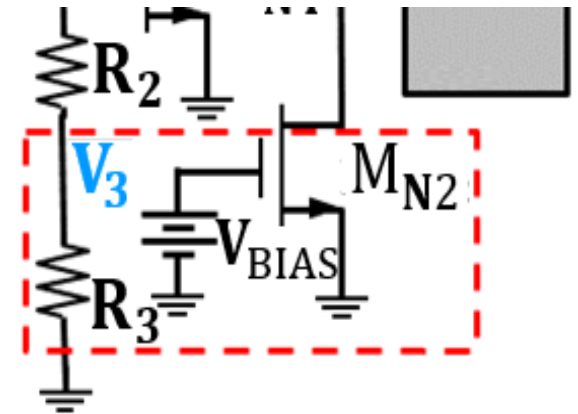
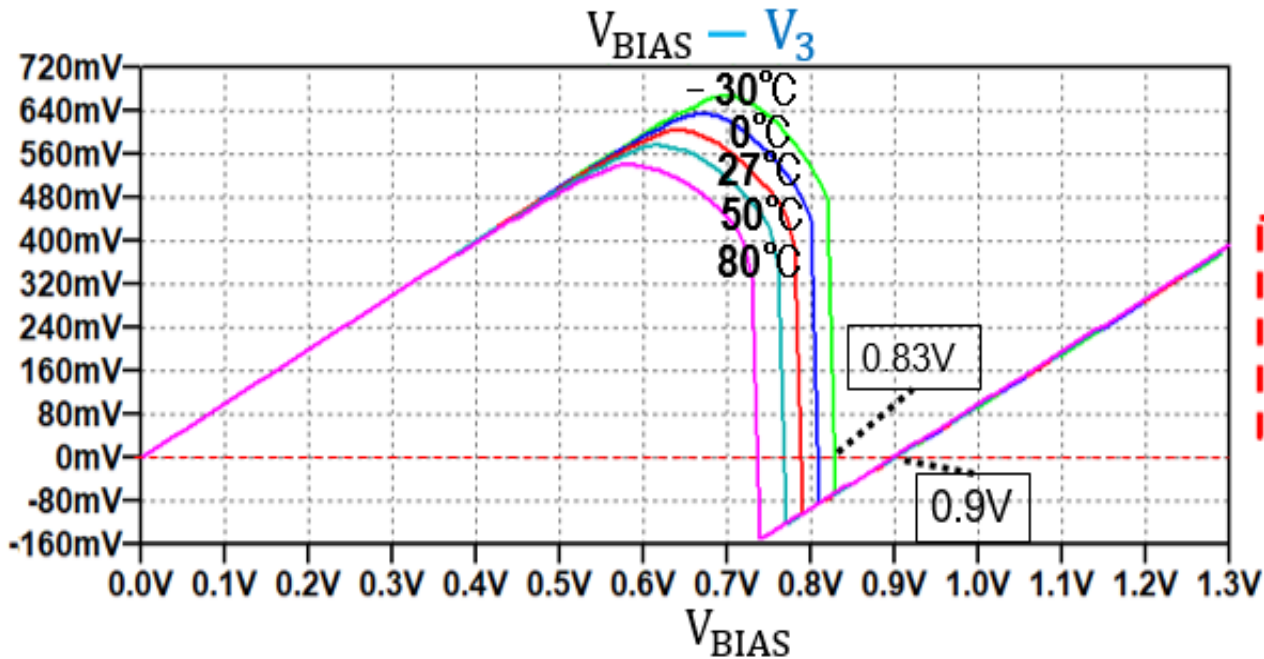


Disconnected loop at node V_3

&

Examine difference between V_{BIAS} and V_3 ($V_{BIAS} - V_3$)

Operation of Open-Loop Circuit

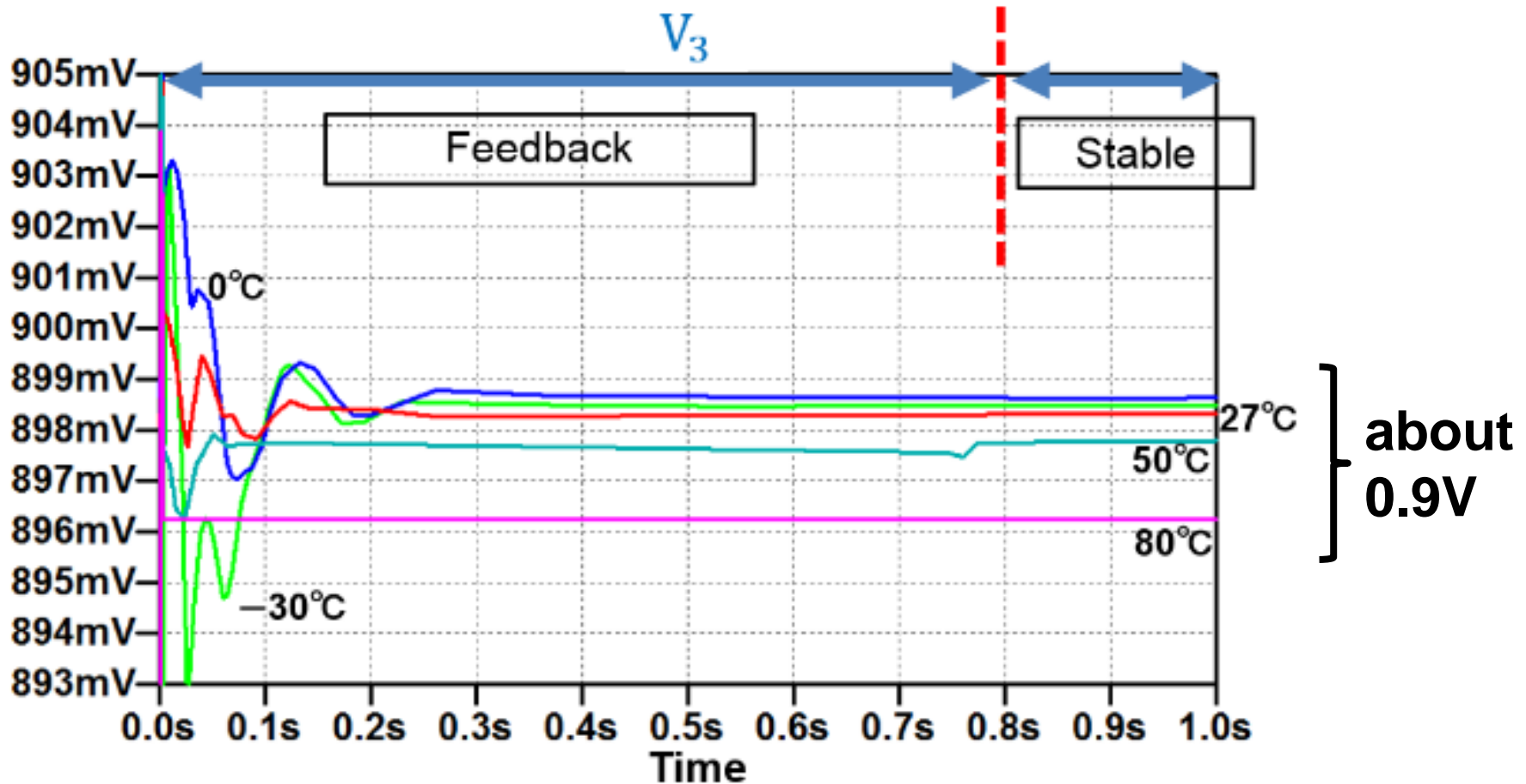


V_{BIAS} vs. $(V_{BIAS} - V_3)$ characteristics of the open-loop circuit

$V_{BIAS} < V_3$: V_3 raises M_{N2} gate voltage

$V_{BIAS} > V_3$: V_3 lowers M_{N2} gate voltage

Negative Feedback Operation



Simulated Negative Feedback Process of V_3

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Conclusion

- **We have proposed temperature-insensitive MOS current source.**
- **Self-bias and startup circuits are used.**
- **Temperature-insensitivity is verified.**
- **Stability is analyzed and verified.**

Remaining work

- **Supply voltage insensitivity confirmation**